

PTO/SB/08A (10-01)

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Substitution for form 1448A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>			Complete If Known		
			Application Number	09/853,233	
			Filing Date	May 11, 2001	
			First Named Inventor	Steven T. Harshfield	
			Art Unit	2823	
			Examiner Name	William D. Coleman	
Sheet	1	of	10	Attorney Docket Number	M4065.0743/P743

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.	Document Number Number-Kind Code ¹ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA	2002/0000686	1/3/2002	Kozicki et al.	
	AB	2002/0168820 App.	11/2002	Kozicki	
	AC	2000/0072188 App.	6/2002	Gilton	
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				Art Unit	2823
				Examiner Name	William D. Coleman
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AS1	6,329,606	12/2001	Freyman et al.	
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Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code ² -Number ³ -Kind Code ⁴ (if known)			
BA	JP 56126916 A		10/19981	Akira et al.	
BB	WO 02/21542		03/14/2002	Kozicki et al.	
BC	WO 00/48196		08/17/2000	Kozicki et al.	
BD	WO 97/48032		12/18/1997	Kozicki et al.	
BE	WO 99/28914		06/10/1999	Kozicki et al.	

Examiner Signature	<i>William D. Coleman</i>	Date Considered	3/26/04
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 509. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² See attached Kind Codes of USPTO Patent Documents at www.uspto.gov or MPEP 801.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 18 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1449B/PTO		Complete If Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	09/853,233
		Filing Date	May 11, 2001
		First Named Inventor	Steven T. Harshfield
		Group Art Unit	2823
		Examiner Name	William D. Coleman
		Attorney Docket Number	M4065.0743/P473
Sheet	3	of	10

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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		Filing Date	May 11, 2001		
		First Named Inventor	Steven T. Harshfield		
		Group Art Unit	2823		
		Examiner Name	William D. Coleman		
Sheet	4	of	10	Attorney Docket Number	M4065.0743/P473

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		Group Art Unit	2823
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Sheet	5	of	10

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		Group Art Unit	2823
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		Attorney Docket Number	M4065.0743/P473
Sheet	6	of	10

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
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Examiner Signature		Date Considered	3/26/04
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